

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)

Docket Number (Optional)

BREV 12370 C

Application Number

Applicant(s)

ASPAR ET AL

Filing Date

Group Art Unit

2823

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EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Dac		5,256,581	10/26/93	FOERSTNER ET AL	437	24	
Dac		6,020,252	2/1/00	ASPAR ET AL	438	458	

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09/17/516
02/06/01

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

D.B. Courts

DATE CONSIDERED

12-21-01

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant:

INFORMATION DISCLOSURE CITATION
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ATTY DOCKET NO.
BREV 12370 CON 2

SERIAL NO. 777516

ASPAR ET AL

FILING

2/6/01

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2823

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Dae	4,704,302	11/3/87	Bruel et al			
	5,234,535	8/10/93	NBeyer et al			
	5,494,835	2/27/96	Bruel			
	5,804,086	9/8/98	Bruel			
	5,817,368	10/6/98	Hashimoto			
	5,863,830	1/26/99	Bruel et al			
	5,897,331	4/27/99	Sopori			
	5,633,174	5/27/97	Li			
Y	5,250,446	10/5/93	Osowa et al			

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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
Dae	WO95/20824	8/3/95	PCT			✓	
	EP 0703 609	3/27/96	EPO			✓	
	0 660 140	6/28/95	EPO			✓	
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Docket Number (Optional)
BREV 12370 CON

Application Number
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Aspar et al

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FORM PTO-1449	SERIAL NO.	CASE NO. BREV 12370 CON 2
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE	GROUP ART UNIT
(use several sheets if necessary)	APPLICANT(S):	Aspar et al.

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

U.S. PATENTS

<u>PATENT NO.</u>	<u>INVENTOR</u>	<u>ISSUE DATE</u>
4,179,324	12/18/79	Kirkpatrick
5,110,748	5/5/92	Sarma
5,310,446	5/10/94	Konishi et al.
5,661,333	8/26/97	Bruel et al.

FOREIGN PATENTS

<u>DOCUMENT NO.</u>	<u>COUNTRY</u>	<u>DATE</u>
2725074	France	March 29, 1996
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Silicon-On-Insulator, European Semiconductor, March, 1997, pages 17 and 18

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FORM PTO-1449	SERIAL NO. 777516	CASE NO. BREV 12370 CON 2
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE 2/6/01	GROUP ART UNIT 2823
(use several sheets if necessary)	APPLICANT(S): Aspar et al.	

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
Dme	A1	4,179,324	12/18/79	Kirkpatrick	156/230	11/28/77
	A2	5,110,748	5/5/92	Sarma	437/51	7/22/91
	A3	5,310,446	5/10/94	Konishi et al.	117/58	7/13/92
	A4	5,661,333	8/26/97	Bruel et al.	257/618	1/25/95
	A5					
	A6					
	A7					
	A8					

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES NO
Dme	A9	2725074	3/29/96	France		X
	A10	0355913	2/28/90	EPO		X
	A11	0504714	9/23/92	EPO		X

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Dme	A12	Silicon-On-Insulator, <i>European Semiconductor</i> , March, 1997, pages 17 and 18
	A13	Aspar et al., SMART-CUT®: The basic fabrication process for UNIBOND® SOI wafers, <i>SEMI</i> 1996, pp. 37-46
	A14	Klem et al., Characteristics of lift-off fabricated AlGaAs/InGaAs single-strained quantum well structures on glass and silicon substrates, <i>Inst. Phys. Conf., Ser. No 96: Chapter 6</i> , pp. 387-392
	A15	Hamaguchi et al., Device Layer Transfer Technique using Chemo-Mechanical Polishing, <i>Japanese Journal of Applied Physics</i> , 23(1984), Oct., No. 10, Part 2, Tokyo, Japan, pp. L815-L817
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EXAMINER D.M. Collins	DATE CONSIDERED 12-21-01
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SERIAL NO. 777516
ASPAR ET AL
FILING 2/6/01 GROUP 2823

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Dme	4,931,405	06/05/1990	KAMIJO ET AL	437	12	
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						YES	NO
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Dme		WILLIAM PRIMAK ET AL IMPURITY EFFECT IN THE IONIZATION DILATATION OF VITREOUS SILICA 1967

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BREV 12370 CON 2		777 516
Applicant(s) ASPAR ET AL		
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BREV 12370 CON	777516
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	H. MORICEAU ET AL, A NEW CHARACTERIZATION PROCESS USED TO QUALIFY SOI FILMS, 1991 PAGES 173-178
	A.J. AUBERTON-HERVE ET AL., SOI MATERIALS FOR ULSI APPLICATION, 1995,
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(also form PTO-1449)

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APPLICANT(S)

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<p><i>Dme</i></p>			La Formation Des Cloques, Saint-Jacques, Nuclear Instruments and Methods 209/210 (1983), pgs. 333-343
<p><i>Dme</i></p>			Hydrogen interaction with phosphorus ion implanted silicon, Tonini, Monelli, Corni, Ottaviani, Frabboni, Canteri, Queirolo Ion Implantation Technolocay - 94, pgs 801-804

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BREV 12370 CON		777516
APPLICANT(S) ASPAR ET AL		
FILING DATE	2/6/01	GROUP 2823

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<p>one</p>		<p>Helium Bubble and Blister Formation for Nickel and An AMorphous Fe-Ni-Mo-B Alloy During 5 keV He+-Irradiation at Temperatures Between 200 K and 600 K, Swijgenhoven, Stals and Knuyt, Nuclear Instruments and Methods 209/210 (1983) pgs. 461-468</p>
<p>one</p>		<p>Infrared Spectroscopy of chemically bonded hydrogen at voids and defects in silicon, Stein, Myers and Follstaedt, J. Appl. Phys. 73(b6), 15 March 1993, pgs. 2755-2764</p>

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Dmc		Silicon-on-insulator produced by helium implantation and thermal oxidation, Raineri, Campisano, Appl. Phys. Lett. 66 (26), 26 June 1995, pgs. 3654-3656
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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE
(Modified) PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(Use several sheets if necessary)

(37 CFR 1.98(b))

ATTY. DOCKET NO.

BREV 12370 CON 2

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Dmc	5 3 7 4 5 6 4	12/20/94	Bruehl	437	24	
	5 4 1 3 9 5 1	5/9/95	Ohori et al	437	61	
	5 5 2 4 3 3 9	6/11/96	Gorowitz et al	29	841	
	5 5 5 9 0 4 3	9/24/96	Bruehl	437	24	
	5 5 6 7 6 5 4	10/22/96	Beilstein, Jr. et al	437	209	
	5 6 1 8 7 3 9	4/8/97	Takabashi et al	438	158	
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	DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
Dmc	7 0 3 6 0 9 A1	3/27/96	EPO	H01L	21/762		X
	5 3 3 5 5 1 A1	9/15/92	EPO	H01L	21/265		X
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Dmc	"Silicon on insulator Material Technology" Bruehl, M.
	Electronic Letters; 31 (1995) 06 July; No. 14; pgs 1201-1202
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EXAMINER

D. M. COUZINS

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